MOSFETs Silicon Carbide N-Channel MOS

TW027Z65C

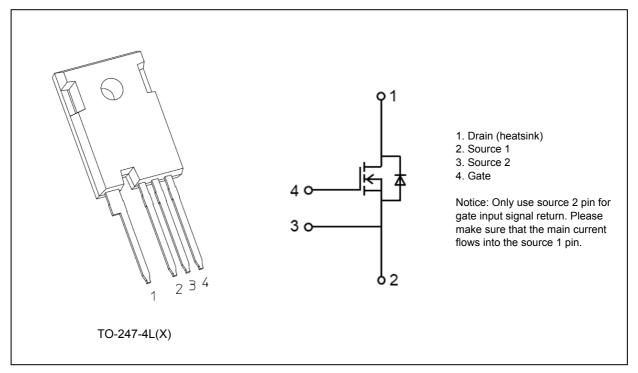
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Chip design of 3rd generation (Built-in SiC schottky barrier diode)
- (2) Low diode forward voltage: $V_{DSF} = -1.35 V$ (typ.)
- (3) High voltage: $V_{DSS} = 650 \text{ V}$
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 27 \text{ m}\Omega$ (typ.)
- (5) Less susceptible to malfunction due to high threshold voltage: V_{th} = 3.0 to 5.0 V (V_{DS} = 10 V, I_D = 3 mA)
- (6) Recommended gate source drive voltage: $V_{GS_{on}} = 18 \text{ V}, V_{GS_{off}} = 0 \text{ V}$
- (7) Enhancement mode.

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25 \ ^{\circ}C$ unless otherwise specified)

	Characteristics	Symbol	Rating	Unit	
Drain-source voltage			V _{DSS}	650	V
Gate-source voltage			V _{GSS}	+25/-10	
Drain current (DC)	(T _c = 25 °C)	(Note 1)	Ι _D	58	A
Drain current (DC)	(T _c = 100°C)	(Note 1)	Ι _D	42	
Drain current (pulsed)	(T _c = 25 °C)	(Note 1)	I _{DP}	170	
Drain current (pulsed)	(T _c = 100°C)	(Note 1)	I _{DP}	128	
Power dissipation	(T _c = 25°C)		PD	156	W
Channel temperature			T _{ch}	175	°C
Storage temperature			T _{stg}	-55 to 175]
Mounting torque			TOR	0.8	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	0.961	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	50	

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care. It should be used for switching applications.

6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	V _{GS} = +25/-10 V, V _{DS} = 0 V	_	_	±0.1	μA
Drain cut-off current		I _{DSS}	V _{DS} = 650 V, V _{GS} = 0 V		7	100	
			T _a = 150 °C, V _{DS} = 650 V, V _{GS} = 0 V	—	37	—	
Drain-source breakdown voltage		V _{(BR)DSS}	I _D = 4 mA, V _{GS} = 0 V	650	—	—	V
Gate threshold voltage	(Note 2)	V _{th}	V _{DS} = 10 V, I _D = 3 mA	3.0		5.0	
Drain-source on-resistance		R _{DS(ON)}	V _{GS} = 18 V, I _D = 29 A	_	27	38	mΩ
			T _a = 150 °C, V _{GS} = 18 V, I _D = 29 A	_	31	—	

Note 2: Please be sure to apply I_{GSS} (V_{GS} = 25 V) before the V_{th} test.

6.2. Dynamic Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 400 V, V _{GS} = 0 V,	_	2288	_	pF
Reverse transfer capacitance	C _{rss}	f = 100 kHz		6.6	_	
Output capacitance	C _{oss}	1	_	249	_	
Effective output capacitance (energy related)	C _{o(er)}		_	288	—	
Effective output capacitance (time related)	C _{o(tr)}		—	413	—	
Output charge	Q _{oss}			165	_	nC
C _{oss} stored energy	E _{oss}	1	_	23	_	μJ
Gate resistance	r _g	V _{DS} = OPEN, f = 1 MHz	_	2.1	_	Ω
Turn-on delay time	t _{d(on)}	See Fig. 6.2.1	_	30	_	ns
Switching time (rise time)	tr	7		15	_	1
Turn-off delay time	t _{d(off)}			42		
Switching time (fall time)	t _f			18	_	
Turn-on switching loss	Eon	7		163		μJ
Turn-off switching loss	E _{off}	7	_	100	_]

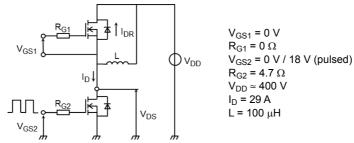


Fig. 6.2.1 Switching Time Test Circuit

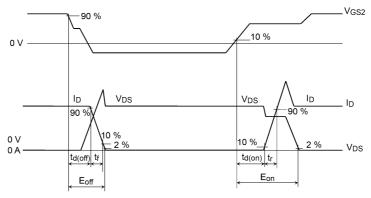


Fig. 6.2.2 Timing Diagrams

6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

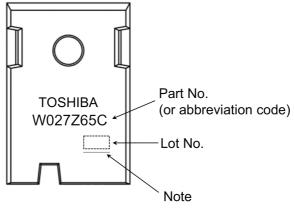
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, \text{ V}_{GS}$ = 18 V, I_D = 29 A	_	65	_	nC
Gate-source charge 1	Q _{gs1}		—	26	—	
Gate-drain charge	Q_gd			10	_	

6.4. Source \cdot Drain Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 3)	I _{DR}	T _c = 25 °C, V _{GS} = -5 V	_	_	44	А
			T _c = 100 °C, V _{GS} = -5 V		_	29	
			T _c = 25 °C, V _{GS} = 18 V	_	_	58	
			T _c = 100 °C, V _{GS} = 18 V			42	
Reverse drain current	(Note 3)	I _{DRP}	T _c = 25 °C, V _{GS} = -5 V		_	163	
(pulsed)			T _c = 100 °C, V _{GS} = -5 V	_	_	75	
			T _c = 25 °C, V _{GS} = 18 V		_	170	
			T _c = 100 °C, V _{GS} = 18 V			128	
Diode forward voltage		V _{DSF}	I _{DR} = 21 A, V _{GS} = -5 V	_	-1.35	-1.80	V
			T _a = 150 °C, I _{DR} = 21 A, V _{GS} = -5 V	—	-1.57	—	
Reverse recovery time		t _{rr}	I _{DR} = 19 A, V _{GS} = 0 V,		55	_	ns
Reverse recovery charge		Q _{rr}	V _{DD} = 400 V, -dI _{DR} /dt = 1000 A/μs	_	358	—	nC
Peak reverse recovery current		I _{rr}		—	13	_	A

Note 3: Ensure that the channel temperature does not exceed 175 °C.

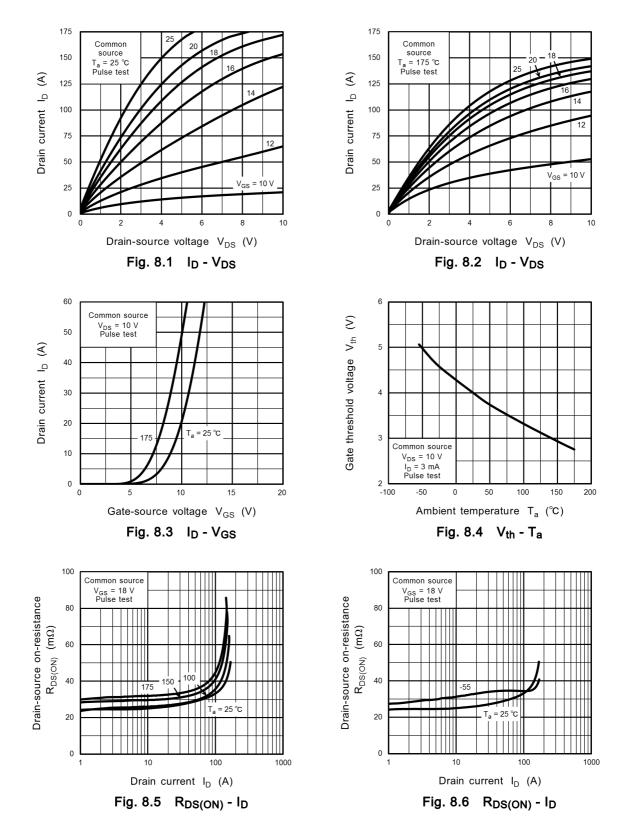
7. Marking (Note)

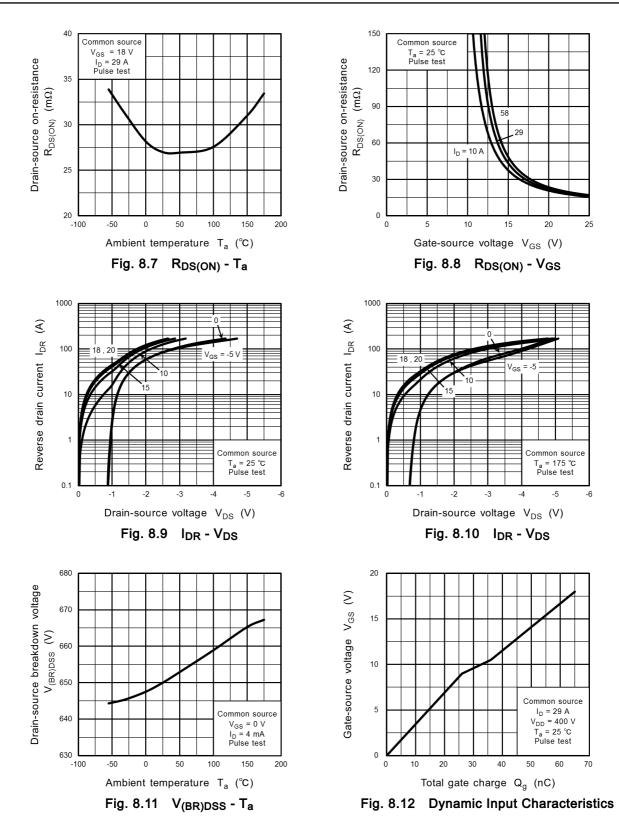


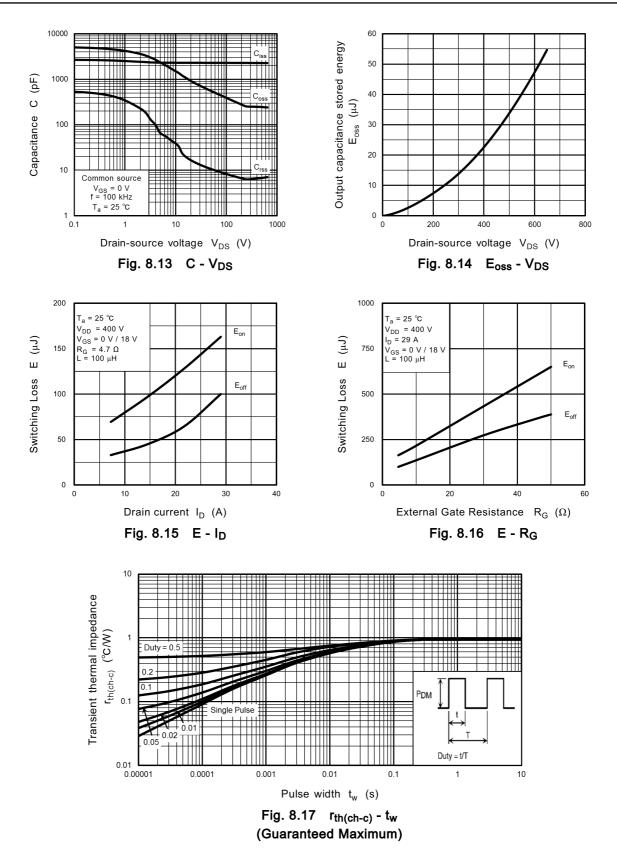


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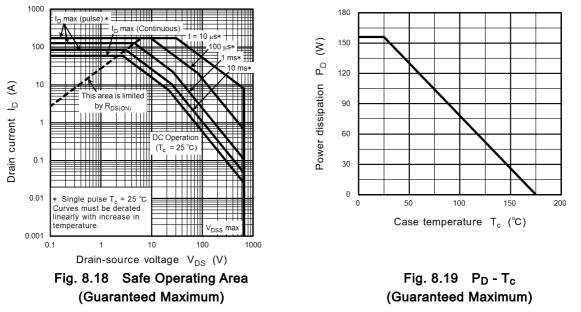
8. Characteristics Curves (Note)

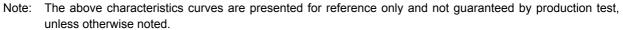








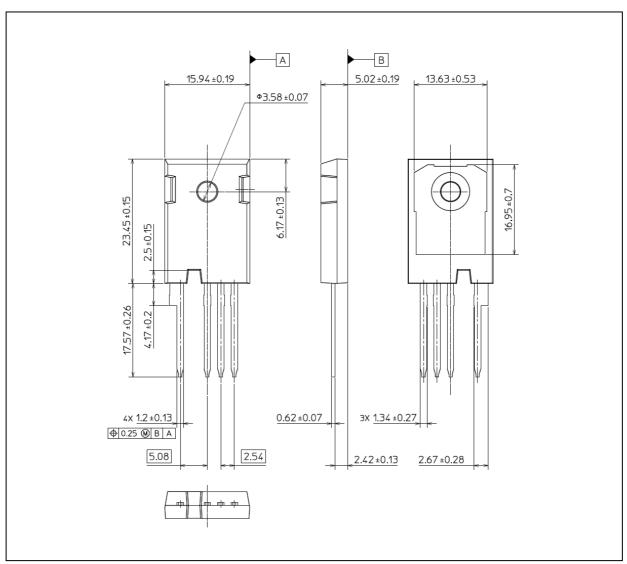




TW027Z65C

Package Dimensions

Unit: mm



Weight: 6.55 g (typ.)

Package Name(s)
TOSHIBA: 2-16M3A
Nickname: TO-247-4L(X)

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